

MEMORY

CMOS 256K x 16 BIT FAST PAGE MODE DYNAMIC RAM

MB81V4260S -60/-70

CMOS 262,144 x 16 bit Fast Page Mode Dynamic RAM

■ DESCRIPTION

The Fujitsu MB81V4260S is a fully decoded CMOS Dynamic RAM (DRAM) that contains 4,194,304 memory cells accessible in 16-bit increments. The MB81V4260S features a "fast page" mode of operation whereby high-speed access of up to 512x16-bits of data can be selected in the same row. The MB81V4260S-60/-70 DRAMs are ideally suited for memory applications such as embedded control, buffer, portable computers, and video imaging equipment where very low power dissipation and high bandwidth are basic requirements of the design.

The MB81V4260S is fabricated using silicon gate CMOS and Fujitsu's advanced four-layer polysilicon process. This process, coupled with three-dimensional stacked capacitor memory cells, reduces the possibility of soft errors and extends the time interval between memory refreshes.

■ ABSOLUTE MAXIMUM RATINGS (see NOTE)

Parameter	Symbol	Value	Unit
Voltage at any pin relative to VSS	V_{IN}, V_{OUT}	-0.5 to +4.6	V
Voltage of V_{CC} supply relative to VSS	V_{CC}	-0.5 to +4.6	V
Power Dissipation	PD	1.0	W
Short Circuit Output Current	I_{OUT}	50	mA
Storage Temperature	T_{STG}	-55 to +125	°C
Temperature under Bias	T_{BIAS}	0 to +70	°C

NOTE: Permanent device damage may occur if the above **Absolute Maximum Ratings** are exceeded. Functional operation should be restricted to the conditions as detailed in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields. However, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.